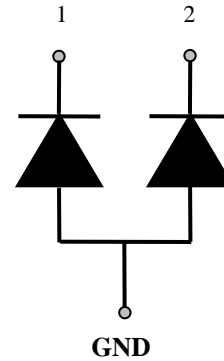
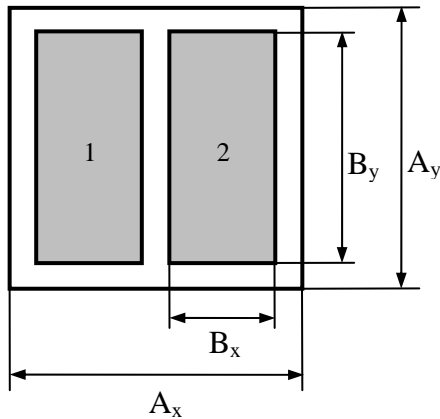


LCD-150P1

Dual chip low capacitance diode on P+ type substrate.



Mechanical date: $A_x=680\mu\text{m}$, $A_y=630\mu\text{m}$.
 $B_x=200\mu\text{m}$, $B_y=475\mu\text{m}$

Chip thickness: $230\pm 12\mu\text{m}$

Scribe Line width - $60\mu\text{m}$.

Top Metal: Al - for wire bonding.

Back side - Anode: Ti-Ni-Ag for soldering.

Schematic and pinning diagram.

Limiting values

Parameter	Symbol	Conditions	Value	Unit
Reverse Stand-off voltage	V_{RWM}	-	5	V
Peak Pulse Power	P_{pp}	$t_p=8/20\mu\text{s}$	25*	W
Peak Pulse Current	I_{pp}	$t_p=8/20\mu\text{s}$	16,0*	A
Electrostatic Discharge	V_{ESD}	IEC 61000-4-2, level 4.	>8 (Contact); >15 (Air).	kV
Max.junction temperature	T_j	-	+150	°C

Characteristics ($T_j=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{BR}	Breakdown voltage	$I_R=1\text{mA}$	50,0	-	-	V
I_R	Reverse leakage current	$V_R=50,0\text{V}$	-	-	0,9	μA
V_F	Peak forward voltage	$I_F=1\text{A}$, $t_p=8/20\mu\text{s}$ $I_F=5\text{A}$, $t_p=8/20\mu\text{s}$ $I_F=16,0\text{A}$, $t_p=8/20\mu\text{s}$	-	-	1,45 2,5* 5,0*	V
C_J	Diode capacitance	$V_R=0\text{V}$, $f=1\text{MHz}$	-	-	5,0	pF

*- For Device testing